

5,827,773

Examiner's Notes

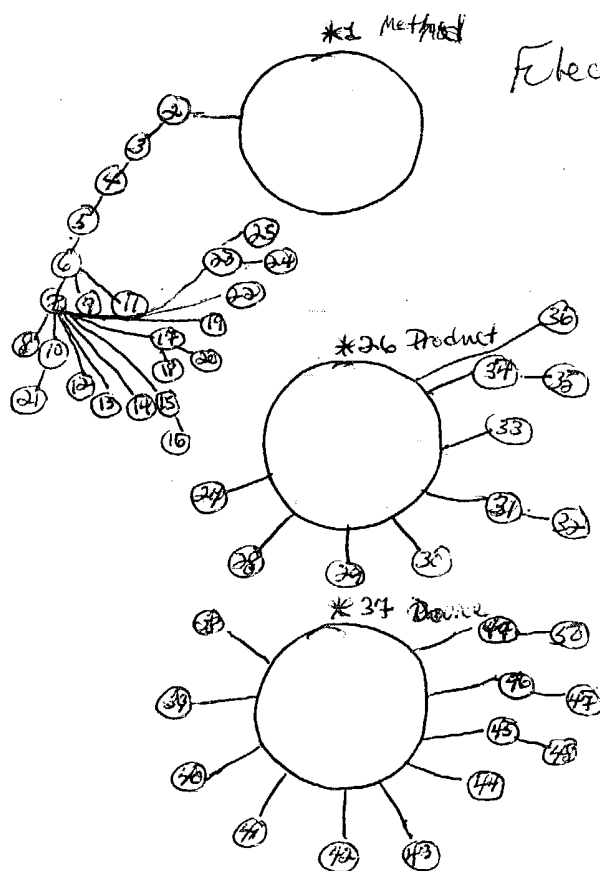
117/092

10/602,186

103 Rej Claims 1-6, 8 and 10

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Allowable Subject Matter!
Objected To Claims 7, 9 and 11-25



Electrode Group I (Claims 1-25)

Motivation: In order to have an annealing process that could be desired & controlled w/ the grain orientation of crystals in a significant region of S.C. film) to have a significant region of S.C. film with a controlled, single crystal orientation to enhance the predictability of device performance.

8.08 1) [51-25 are]

2) [A mtd for forming a SC film single crystal domains.]

MTD
I 3) [117]

4) [92]

5) [526-36 are]

6) [A semiconductor structure w/ lateral single crystal]

7) [428]

Prod
II 8) [14]

8.09 1) [537-50 are]

2) [A single-crystal thin-film transistor (TFT).]

App
III 3) [438]

4) [14]

I → II

I → III

II → III